

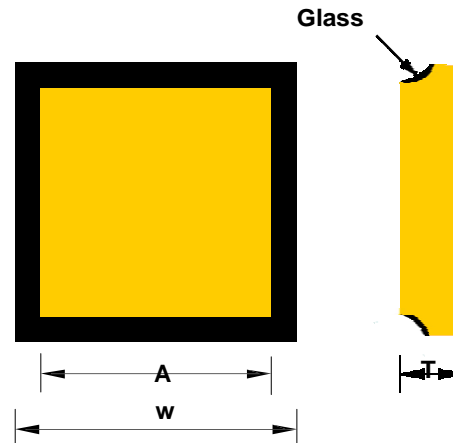


## DGS60 THRU DGS70

### General Purpose Rectifier GPP Chips

#### Features

- Fully glass passivated -needs no encapsulation
- Peak reverse voltage to 1800 volts
- Low forward voltage drop( $V_F$ )
- Metallized surface



#### Description

The GPP chips series are diffused silicon, glass passivated rectifier die.

These devices can be supplied to meet customer's requirements.

The prime application for unencapsulated die is in hybrid circuits. For this reason, a variety of metallized surfaces are available.

Gold is standard for wire bonding, and for soldering application, gold flash chips are supplied.

#### Electrical Characteristics ( $T_A = 25^\circ\text{C}$ unless specified)

PARAMETER	SYMBOL	DGS60	DGS70				UNIT
Dimension	W	60±3	70±3				mils
Dimension	A	45±3	57±3				mils
Dimension	T	265±8					μm
Peak Inverse Voltage	$V_B$	1100					Volts
Forward current	$I_F$	1.5~2.0	2.0				Amps
Forward Voltage Drop	$V_F$	≤0.98	≤0.98				Volts
Forward Surge current	$I_{FSM}$	50	50				Amps
Reverse Recovery Time	$T_{RR}$	≥ 1000	≥ 1000				ns
Junction Temperature	$T_{JFM}$	175	175				°C
Reverse Current at 25°C	$I_R$	2	2				μA
Storage Temperature	$T_{ST}$	-65 --- 175					°C
Die attach Temperature	$T_d$	375					°C

Note :

Other dimension of GPP chip ranging from 42 mils to 600 mils which is not specified on the list, can also be supplied by special procurement agreement.